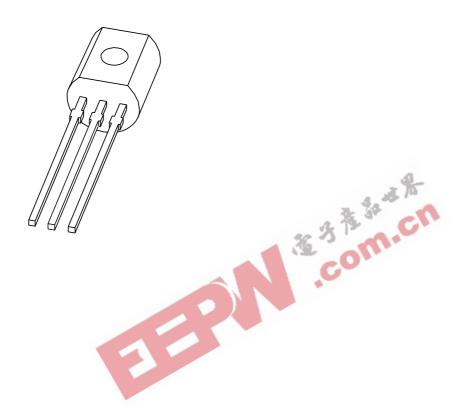
## **DISCRETE SEMICONDUCTORS**

# DATA SHEET



## 2N3904 NPN switching transistor

Product specification Supersedes data of 1999 Apr 23 2004 Oct 11





## **NPN** switching transistor

2N3904

#### **FEATURES**

- Low current (max. 200 mA)
- Low voltage (max. 40 V).

#### **APPLICATIONS**

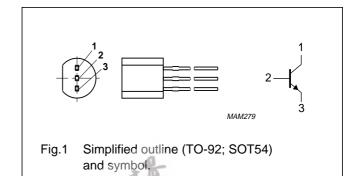
• High-speed switching.

#### **DESCRIPTION**

NPN switching transistor in a TO-92; SOT54 plastic package. PNP complement: 2N3906.

#### **PINNING**

PIN	DESCRIPTION
1	collector
2	base
3	emitter



#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
TYPE NUMBER	NAME	DESCRIPTION	VERSION
2N3904	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS			
V <sub>CBO</sub>	collector-base voltage	open emitter	_	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	6	V
I <sub>C</sub>	collector current (DC)		_	200	mA
I <sub>CM</sub>	peak collector current		_	300	mA
I <sub>BM</sub>	peak base current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## NPN switching transistor

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	250	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C.

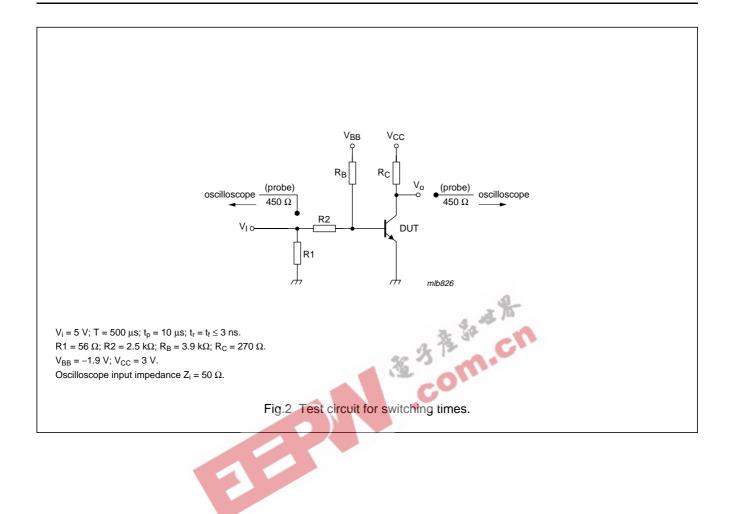
SYMBOL	PARAMETER CONDITIONS			MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A	_	50	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 6 V; I <sub>C</sub> = 0 A	_	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; note 1			
		I <sub>C</sub> = 0.1 mA	60	_	
		I <sub>C</sub> = 1 mA	80	_	
		I <sub>C</sub> = 10 mA	100	300	
		I <sub>C</sub> = 50 mA	60	_	
		$I_C = 1 \text{ mA}$ $I_C = 10 \text{ mA}$ $I_C = 50 \text{ mA}$ $I_C = 100 \text{ mA}$ $I_C = 100 \text{ mA}$	30	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}$ ; $I_B = 1 \text{ mA}$ ; note 1	_	200	mV
		$I_C = 50 \text{ mA}$ ; $I_B = 5 \text{ mA}$ ; note 1	_	200	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 10 \text{ mA}$ ; $I_B = 1 \text{ mA}$ ; note 1	_	850	mV
		$I_C = 50 \text{ mA}$ ; $I_B = 5 \text{ mA}$ ; note 1	_	950	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = 5 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	_	4	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 500 \text{ mV}; I_C = I_C = 0 \text{ A}; f = 1 \text{ MHz}$	_	8	pF
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 20 V; I <sub>C</sub> = 10 mA; f = 100 MHz	300	_	MHz
F	noise figure	$V_{CE} = 5 \text{ V}; I_{C} = 100  \mu\text{A}; R_{S} = 1  k\Omega;$	_	5	dB
		f = 10 Hz to 15.7 kHz			
Switching t	imes (between 10 % and 90 % leve	<b>ls); see</b> Fig.2			
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 1 mA;	_	65	ns
t <sub>d</sub>	delay time	$I_{Boff} = -1 \text{ mA}$	_	35	ns
t <sub>r</sub>	rise time		_	35	ns
t <sub>off</sub>	turn-off time		_	240	ns
t <sub>s</sub>	storage time		_	200	ns
t <sub>f</sub>	fall time		_	50	ns

#### Note

1. Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ 

## NPN switching transistor

2N3904



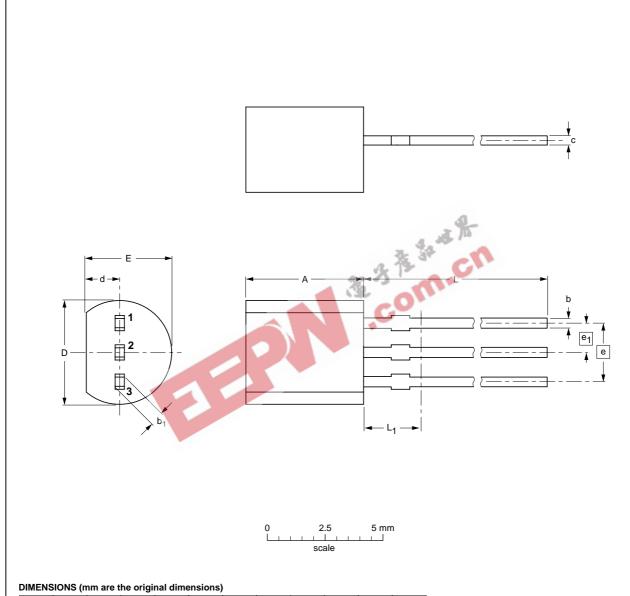
## NPN switching transistor

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#### **PACKAGE OUTLINE**

#### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		KEFER	ENCES		EUROPEAN ISSUE DAT		
RSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A			<del>97-02-28</del> 04-06-28	
	RSION	RSION IEC	RSION IEC JEDEC	RSION IEC JEDEC JEITA	RSION IEC JEDEC JEITA	RSION IEC JEDEC JEITA PROJECTION	

### NPN switching transistor

2N3904

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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Oct 11

Document order number: 9397 750 13544

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